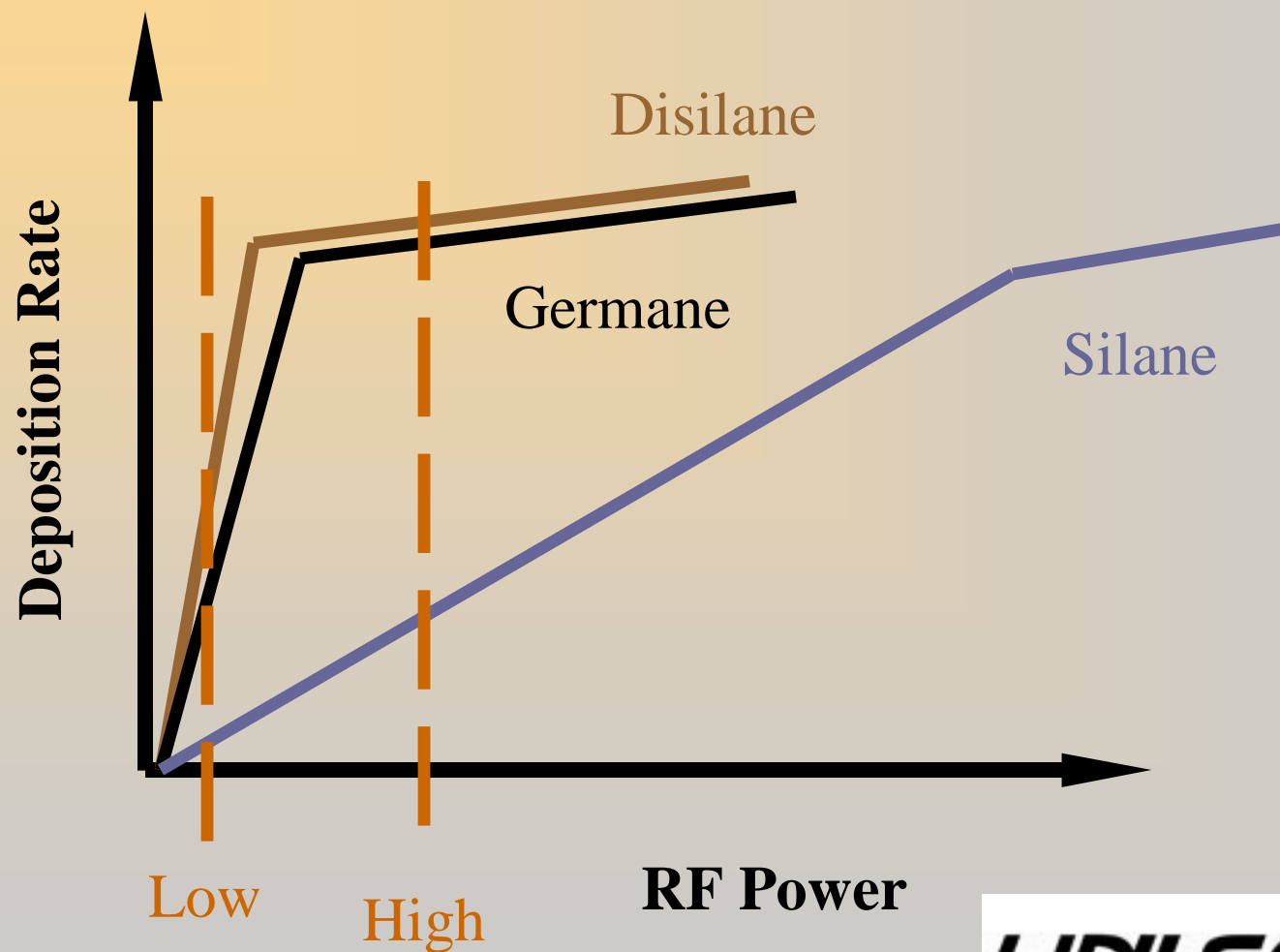


# *a-SiGe - Stabilized Performance and Deposition Rate*

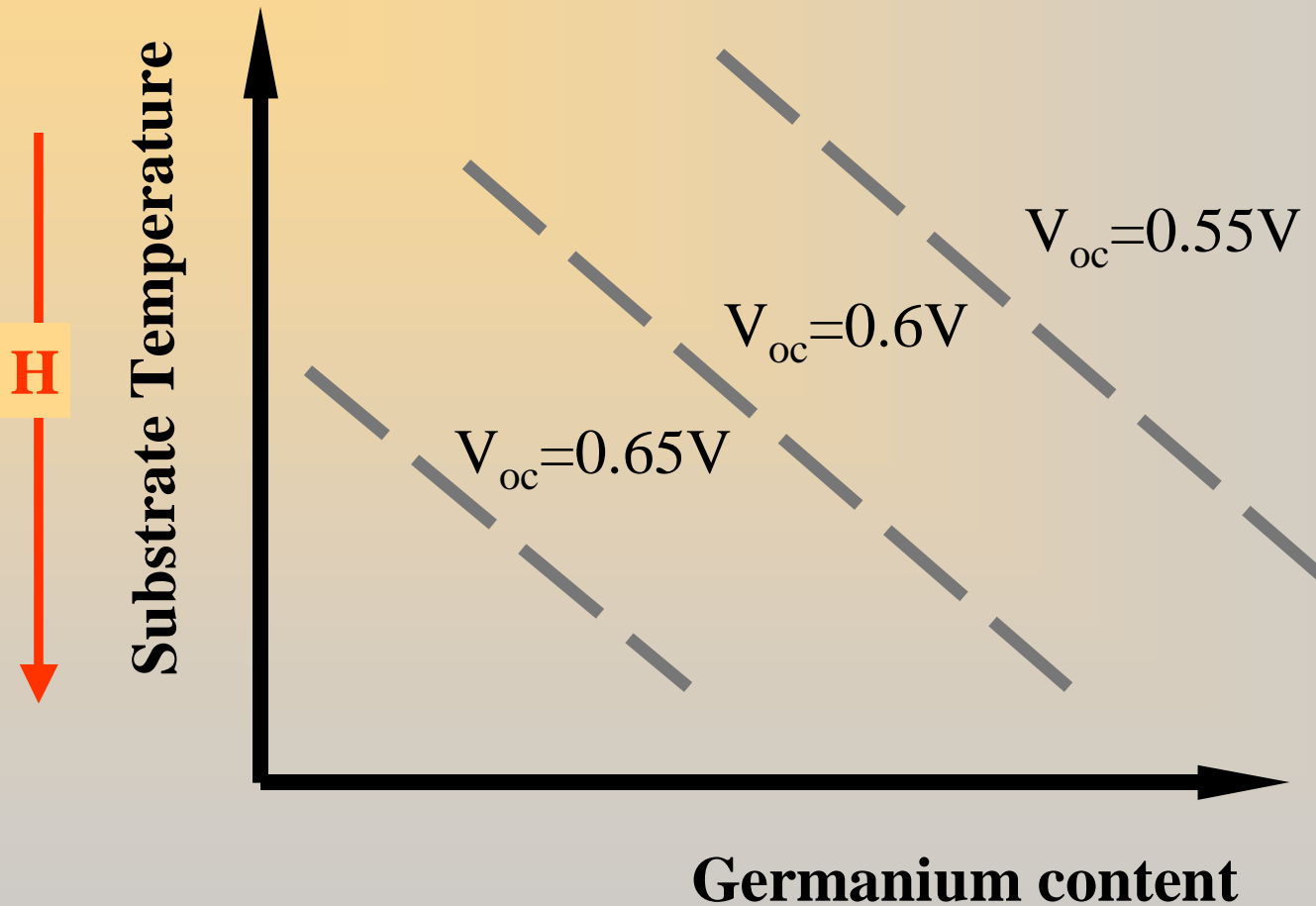
1. Silane instead of disilane at high rate
2. Higher temperature - less germanium
3. Grading optimized for higher rate deposited material



# *From Disilane to Silane*

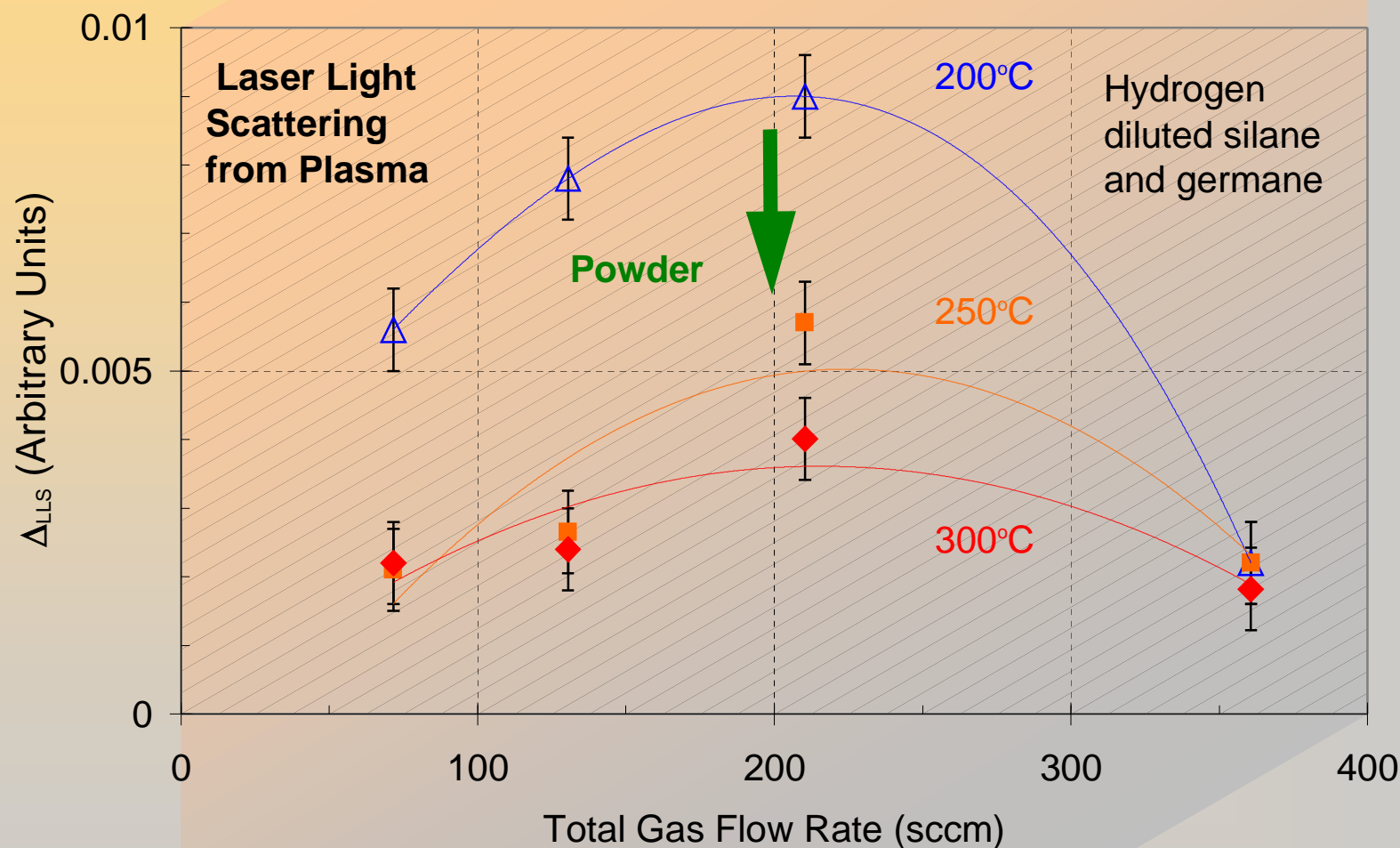


# $V_{oc}$ vs. Ge, *H* content



Adapted from  
Terakura, PhD Thesis

# *Powder decreases at higher $T_s$*



★ Less powder implies more stable  
a-SiGe:H

## *Higher $T_s$ - Less Ge*

Sample	State	$V_{oc}$	FF	$J_{sc}$	$P_{max}$
		(V)		(mA/cm <sup>2</sup> )	(mW/cm <sup>2</sup> )
9890 LC1	Std.	0.601	0.577	7.36	2.55
9887 LC1	Higher	0.59	0.584	7.71	2.66
9904 LC1	Highest	0.613	0.598	7.44	2.73

- ★ Increasing the temperature reduces the hydrogen content and less germanium is required to obtain the same  $V_{oc}$
- ★ The initial performance improves and stability is expected to be better

## *From Disilane to Silane*

Sample	State	V <sub>oc</sub>	FF	J <sub>sc</sub>	P <sub>max</sub>
		(V)		(mA/cm <sup>2</sup> )	(mW/cm <sup>2</sup> )
Disilane					
8364 LC1	initial	0.595	0.644	8.09	3.10
	1012 h	0.565	0.581	7.80	2.60
Silane					
9917 LC1	Initial	0.594	0.583	7.79	2.70
	1008 h	0.571	0.514	7.44	2.18

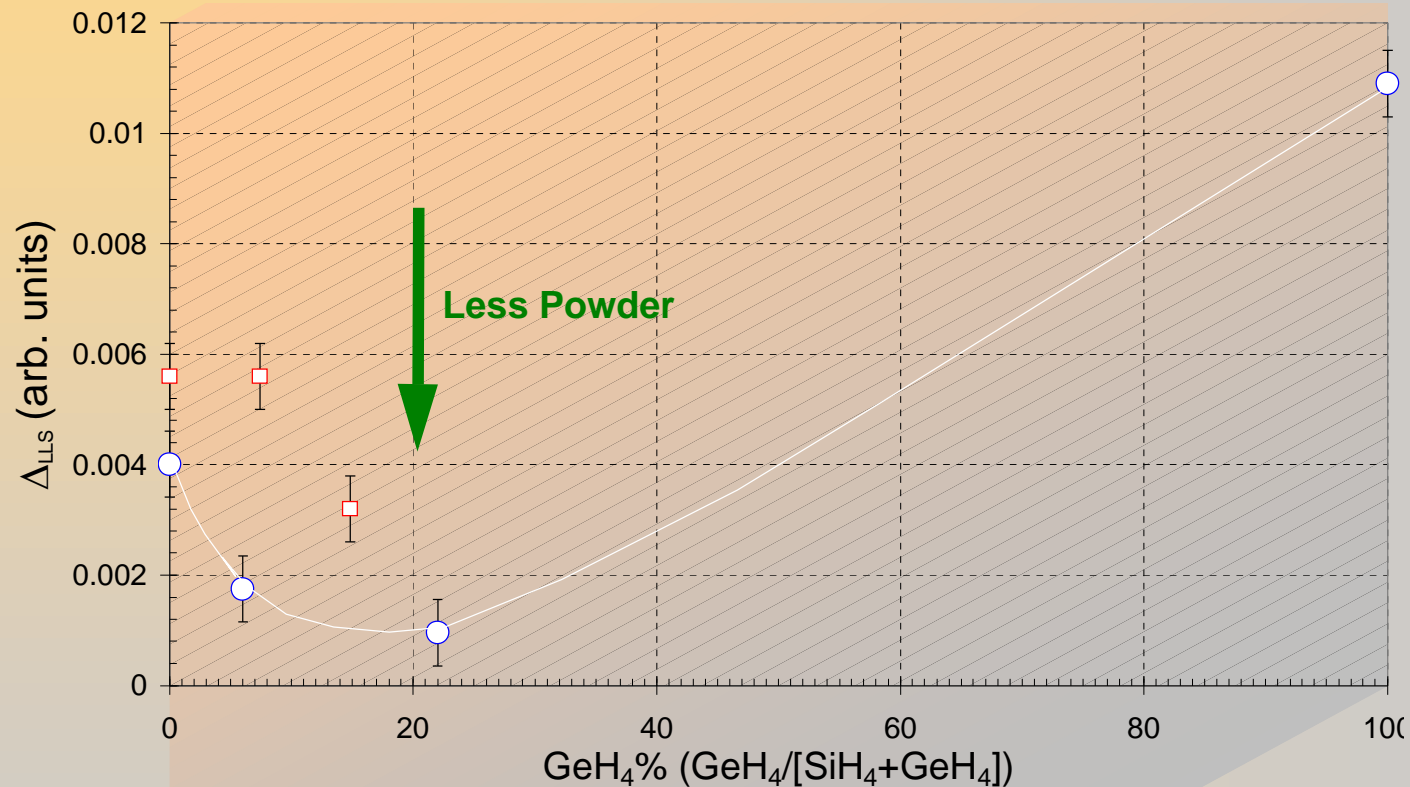
- ★ Bottom cells deposited using ‘production constraints’ (high rate, etc.)
- ★ Performance of bottom cell with silane not quite as good as disilane (84%)

# *Improved Germane Grading*

Sample	State	V <sub>oc</sub>	FF	J <sub>sc</sub>	P <sub>max</sub>
		(V)		(mA/cm <sup>2</sup> )	(mW/cm <sup>2</sup> )
Standard					
9917 LC1	Initial	0.594	0.583	7.79	2.70
	1008 h	0.571	0.514	7.44	2.18
Grading 1					
10044 LC1	Initial	0.594	0.645	7.75	2.97
	1000 h	0.564	0.55	7.36	2.28
Grading 2					
10058 LC1	Initial	0.598	0.649	7.73	3.00
	1000 h	0.566	0.566	7.32	2.35

- ★ Improved performance with Ge grading adapted to higher rate bottom cell
- ★ Performance is 90% of that with disilane

# *Less powder at low Ge/Si*



★ Sweet spot at low germane fraction



# High Rate Middle Cell

Sample	State	V <sub>oc</sub>	FF	J <sub>sc</sub>	P <sub>max</sub>
		(V)		(mA/cm <sup>2</sup> )	(mW/cm <sup>2</sup> )
Disilane					
8316 B0	Initial	0.718	0.697	7.70	3.85
	1055h	0.664	0.598	7.22	2.87
Silane -standard					
9941 LC1	Initial	0.702	0.678	7.37	3.51
	1008h	0.648	0.571	7.08	2.62
Silane -grading 1					
10049 LC1	Initial	0.691	0.694	7.58	3.64
	1000h	0.645	0.586	7.29	2.75
Silane -grading 2					
10046 LC1	Initial	0.685	0.704	7.74	3.73
	1000h	0.639	0.584	7.43	2.77

★ The middle cell also improves to 97% of that with disilane



# *Conclusions*

- ★ We have improved the stable, total area performance of the high rate bottom cell from 2.18 to 2.35 mW/cm<sup>2</sup>
- ★ The middle cell has been improved from 2.62 to 2.77 mW/cm<sup>2</sup>
- ★ Higher temperature, less germanium and grading adapted to higher rate deposited material have been used.